I	Data	Feb.	26th	2016
Ref N	lo.G2	2K-R	-1602	218-2

Prepared: & Hometoni

Approved: 24- milin J. Okang

RF DEVICE DEPT PRODUCTS DIVISION QUALYTY ASSURANCE DEPT PRODUCTS DIVISION MIYOSHI ELECTRONICS CORPORATION

# Subject: Additional production site for MITSUBISHI Silicon RF Power devices(Notification)

We hereby notify you of our decision to have an additoinal production site for our devices. This addition is to increase our production capacity, and the site is original production factory of our SLP products.

Current production site: Microchip Technology(Thailand) Co.,Ltd (MMT) Additional production site: Shimane Masuda Electronics Co.,LTD (SME) (Original production factory of our SLP products)

- 1. No change in the materials for the products
- 2. No change in Products type number
- 3. No change in Specification and outline drawing
- 4. No change in electrical characteristics and reliability test results
- 5. The production site can be identified by Lot-No.

Contents

RF characteristics (RD07MUS2B) Reliability report (RD07MUS2B)

### ●Products subject、Reason of change、Change schedule

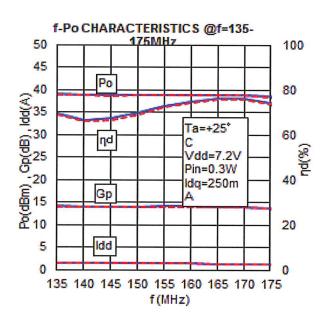
	Product name MOS FET RF Power device.			Type number RD series discrete devices of SLP package			
Subject							
	Reason of change Increase of production capa		on capacity				
	Changed contents Addition of production		site				
			New(add	dition)			
	Production site: THAILAND(MMT)		Produce	tion site: Japan(SI	ME)		
Reason of change	<ul> <li>Country of origin: THAILAND</li> <li>Identification: Lot No.***AA-ZG~***RZ-ZG</li> </ul>		• Identifie	<ul> <li>Country of origin: JAPAN</li> <li>Identification: Lot No.***SA-ZG~***ZZ-ZG</li> <li>Printed "J" on Outer LABEL</li> </ul>			
			Printed	"J" on Outer LAE	3EL		
			·Printed	J" on Outer LAE			
			•Printed	"J" on Outer LAE	2016 Mar.	Apr.	May.
	Notification			Feb.	2016	Apr.	May.
Change	Production at MMT			Feb.	2016 Mar. otification		
	Production at MMT			Feb.	2016 Mar. otification	Apr.	

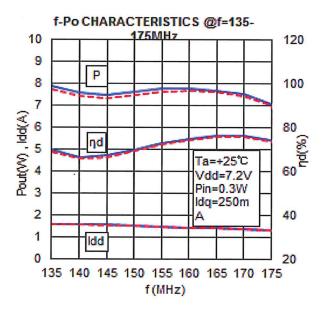
#### VHF-band RF characteristics

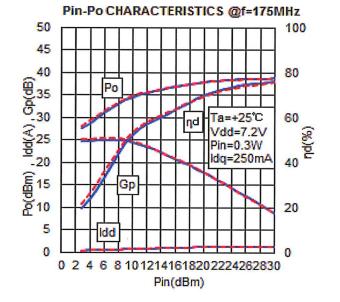
frequency response , Pin-Po characteristics

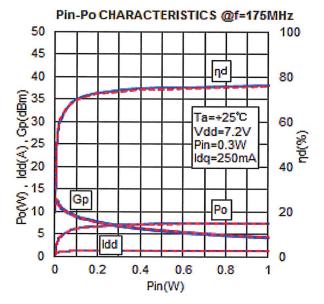
SME-product: Blue line, MMT-products: Broken red line

Result: It is observed that the characteristics of SME products are identical to those of MMT-products







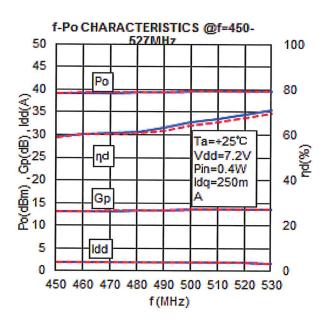


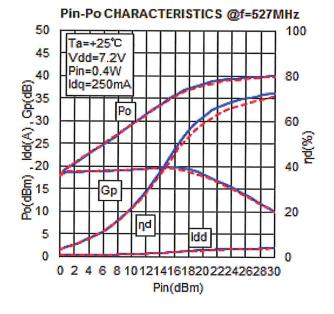
UHF-band RF characteristics

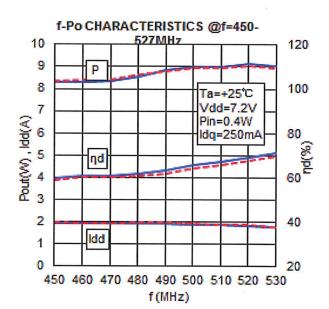
frequency response , Pin-Po characteristics

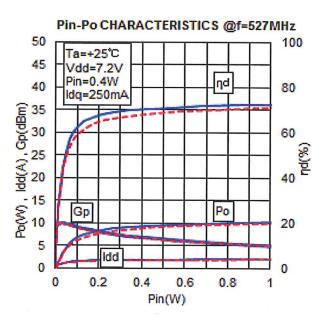
SME-product: Blue line, MMT-products: Broken red line

Result: It is observed that the characteristics of SME products are identical to those of MMT-products







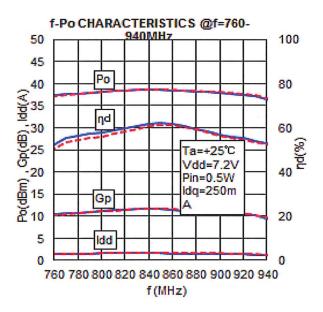


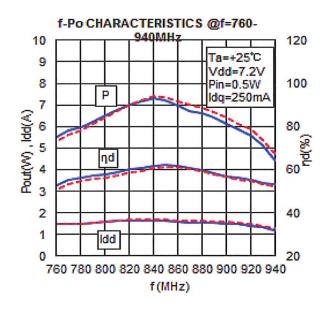
#### ● 800/900MHz-band RF characteristics

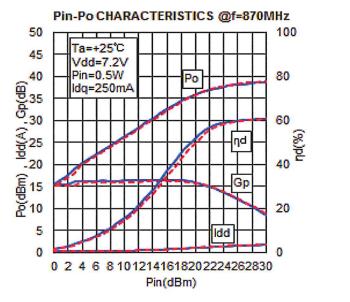
frequency response , Pin-Po characteristics

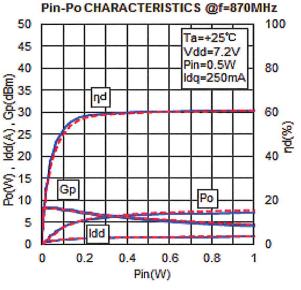
SME-product: Blue line, MMT-products: Broken red line

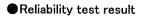
Result: It is observed that the characteristics of SME products are identical to those of MMT-products











#### RD07MUS2B (RoHS Compliance device of SLP outline) reliability results 以下表にRD07MUS2Bにて実施した信頼性試験結果を示します。 The following summarizes reliability test results on RD07MUS2B.

Result : Reliability test result that within failure criteria, same level with current specification.

表1	結果	Table '	Result	

グルーフ゛	試験項目	試験条件	試験数量	故障数QTY of
Group	Test item	Test condition	QTY of sample	failure
1 *	高温保存 High temperature storage	125°C 1000hours	11	0
2 *	低温保存 Low temperature storage	-40°C 1000hr	11	0
3 *	耐湿性保存 Humidity storage	85°C/85%RH 1000hr	11	0
4 *	温度サイクル Temperature cycling	-40°C ∕ 125°C 510cycles 30min/30min	22	0
5 *	熱衝擊 Thermal shock	-40°C ∕ 125°C 100cycles 5min/5min	5	0
6 *	耐基板曲げ Deflection	Distance between fulcrums:90mm Flexure:2mm ,5times	5	0

\* Pre-treatment was done before the tests.

Pre-treatment condition:

Baking:125°C24hr→ Moisture soak:30°C,70%RH,192hr→ Reflow:255°C+5°C,30sec,3time

#### 表2.故障判定基準Table 2 Failure criteria

グループ	試験項目	故障判定基準	
Group	Test	Failure criteria	
1	高温保存 High temperature storage	For Po and kd , More than the following amount	
2	低温保存 Low temperature storage	ΔPo=±20% Δld=±20% @ freq=137MHz Pin=300mW	
3	耐湿性保存 Humidity storage	ldq=250mA(Vgg adj.) Vdd=7.2V Investigation by means of a microscope. Rthj-c = ±20%	
4	温度サイクル Temperature cycling		
5	熱衝撃 Thermal shock	For DC check , and internal visual check. lgss@Vgs=5V,Vds=0V $\leq$ 1uA, ldss@Vds=17V,Vgs=0V $\leq$ 10uA	
6	耐基板曲げ Deflection	Internal visual check: nothing chip crack, open wire, etc.	

## Objective products

specification
RD02MUS1-2**
RD02MUS1-T2**
RD02MUS1B-2**
RD02MUS1B-T2**
RD04LUS2-2**
RD04LUS2-T2**
RD04HMS2-2**
RD04HMS2-T2**
RD07MVS1-2**
RD07MVS1-T2**
RD07MVS1A-2**
RD07MVS1A-T2**
RD07MVS1B-2**
RD07MVS1B-T2**
RD07MVS2-2**
RD07MVS2-T2**
RD07MUS2B-2**
RD07MUS2B-T2**
RD10MMS2-2**
RD10MMS2-T2**
RD12MVS1-2**
RD12MVS1-T2**

Ref No.G2K-R-160218-2